查询SD1006供应商

NPN SILICON HIGH FREQUENCY TRANSISTOR

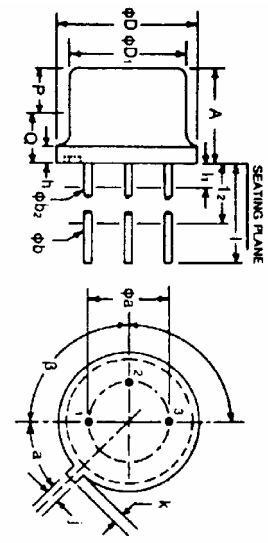
DESCRIPTION:

The **ASI SD1006** is a High Frequency Transistor for General Purpose Amplifier Applications.

MAXIMUM RATINGS

I_C	400 mA
V_{CEO}	30 V
V_{CBO}	50 V
P_{DISS}	3.5 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	50 °C/W

PACKAGE STYLE TO-39



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
φa	0.190	0.210	4.83	5.33
A	0.240	0.260	6.10	6.60
φb	0.016	0.021	0.406	0.533
φb₂	0.016	0.019	0.406	0.483
φD	0.350	0.370	8.89	9.40
φD₁	0.315	0.335	8.00	8.51
h	0.009	0.125	0.229	3.18
j	0.028	0.034	0.711	0.864
k	0.029	0.040	0.737	1.02
l	0.500		12.70	
l₁		0.050		1.27
l₂	0.250		6.35	
P	0.100		2.54	
Q				
a	45° NOMINAL			
β	90° NOMINAL			

1 = EMITTER 2 = BASE
3 = COLLECTOR

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 5.0 mA			30			V
BV_{CBO}	I_C = 100 μA			50			V
BV_{EBO}	I_E = 100 μA			5.0			V
I_{CEO}	V_{CE} = 28 V					100	μA
h_{FE}	V_{CE} = 15 V	I_C = 50 mA		30		300	---
f_t	V_{CE} = 15 V	I_C = 50 mA		1500	1800		MHz
C_{ob}	V_{CB} = 30 V		f = 100 KHz		2.5	3.5	pF
C_{ib}	V_{EB} = 0.5 V		f = 100 KHz		8.0	10	pF
NF_{NB}	V_{CE} = 10 V	I_C = 10 mA	f = 2000 MHz		2.7		dB
NF_{BB}	V_{CE} = 15 V	I_C = 50 mA	f = 216 MHz		7.0	8.0	dB
G_{VE}	V_{CE} = 15 V	I_C = 50 mA	f = 216 MHz		7.2	6.8	dB
X_{MOD}	V_{CE} = 15 V	I_C = 50 mA	P_{out} = +45 dbmV		-60	-57	dB
2_{NDO}	V_{CE} = 15 V	I_C = 50 mA	P_{out} = +45 dbmV		-60	-50	dB